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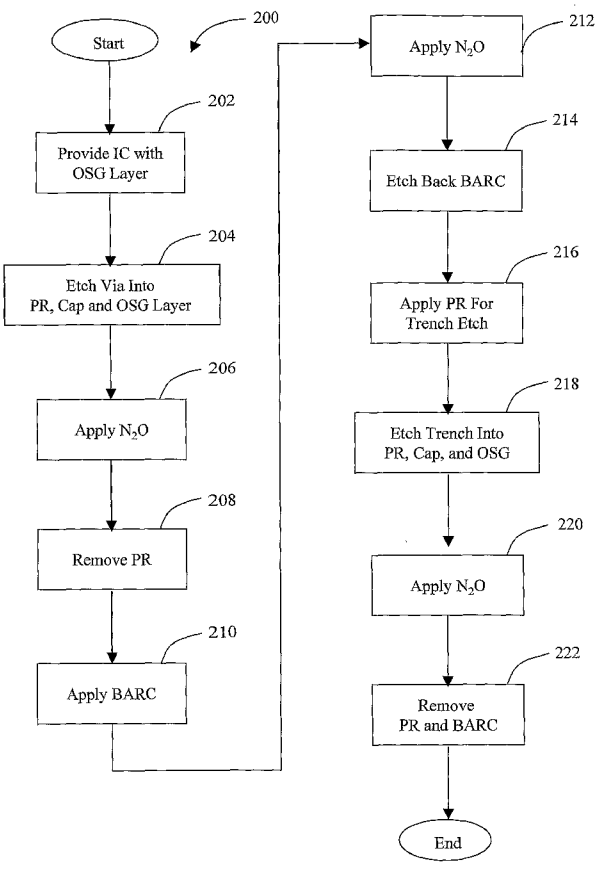
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(54) Title: AN ETCH BACK PROCESS USING NITROUS OXIDE



(57) Abstract: A method for generating an organic plug within a via is described. The via resides in an integrated circuit (IC) structure having a silicon containing dielectric material. The method for generating the organic plug includes applying an organic compound such as a bottom antireflective coating. The organic compound occupies the via. The method then proceeds to feed a nitrous oxide (N_20) gas into a reactor and generates a plasma in the reactor. A significant portion of the organic compound is removed leaving behind an organic plug to occupy the via. The organic plug is typically generated during dual damascene processing.

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